



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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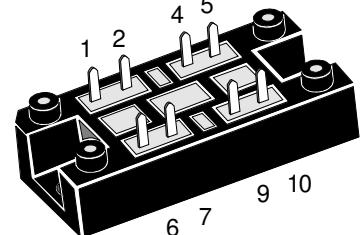
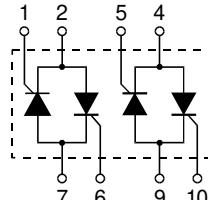
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AC Controller Modules

$I_{RMS} = 2 \times 30 \text{ A}$
 $V_{RRM} = 800-1600 \text{ V}$

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
800	800	VW2x30-08io1
1200	1200	VW2x30-12io1
1400	1400	VW2x30-14io1
1600	1600	VW2x30-16io1



Symbol	Test Conditions	Maximum Ratings		
I_{RMS}	$T_c = 85^\circ\text{C}$, (per phase)	30	A	
I_{TRMS}	$T_{VJ} = T_{VJM}$	22	A	
I_{TAVM}	$T_c = 85^\circ\text{C}$; (180° sine ; per thyristor)	14	A	
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	200 210	A A	
	$T_{VJ} = T_{VJM}$ $V_R = 0$	180 190	A A	
I^2t	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	200 190	A^2s A^2s	
	$T_{VJ} = T_{VJM}$ $V_R = 0$	160 150	A^2s A^2s	
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 50 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.45 \text{ A}$ $di_G/dt = 0.45 \text{ A}/\mu\text{s}$	repetitive, $I_T = 45 \text{ A}$ non repetitive, $I_T = I_{TAVM}$	100 500	$\text{A}/\mu\text{s}$ $\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$	1000	$\text{V}/\mu\text{s}$
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$ $t_p = 300 \mu\text{s}$	10 5	W W
P_{GAVM}			0.5	W
V_{RGM}			10	V
T_{VJ}			-40...+125	$^\circ\text{C}$
T_{VJM}			125	$^\circ\text{C}$
T_{stg}			-40...+125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	3000 3600	V_\sim V_\sim
M_d	Mounting torque (M5)		2-2.5/18-22	Nm/lb.in.
Weight	typ.	35	g	

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.
 IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values		
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	5	mA
V_T	$I_T = 45 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.81	V
V_{TO}	For power-loss calculations only		0.8	V
r_T			25	$\text{m}\Omega$
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	\leq	1.5	V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	\leq	100	mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	\leq	0.2	V
I_{GD}		\leq	5	mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	\leq	450	mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	200	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	\leq	2	μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_p = 200 \mu\text{s}; di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	150	μs
R_{thJC}	per thyristor; DC		1.7	K/W
	per module		0.43	K/W
R_{thJK}	per thyristor; DC		2.0	K/W
	per module		0.5	K/W
d_s	Creeping distance on surface		12.7	mm
d_A	Creepage distance in air		9.4	mm
a	Max. allowable acceleration		50	m/s^2

Dimensions in mm (1 mm = 0.0394")

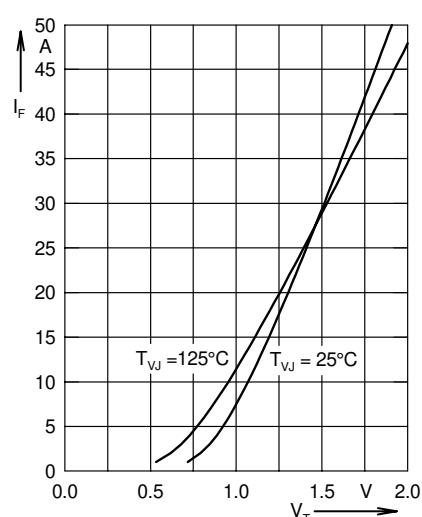
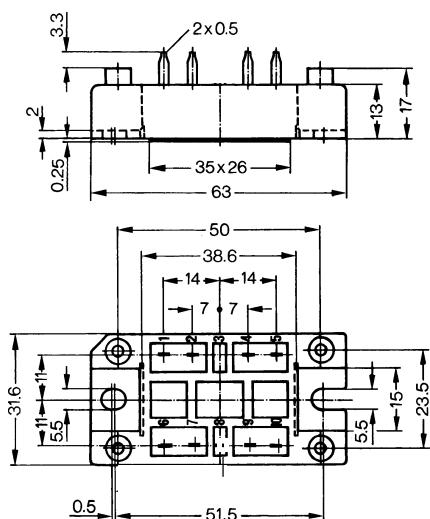


Fig. 3 Forward current versus voltage drop per leg

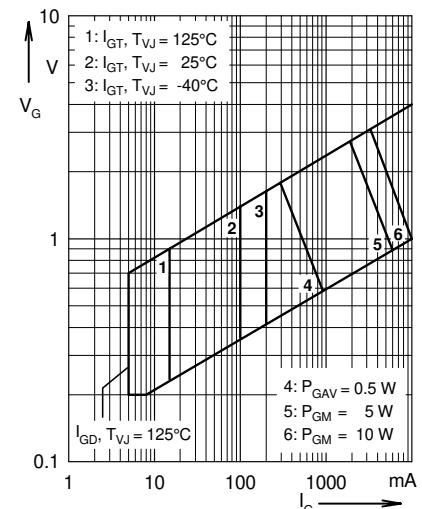


Fig. 1 Gate trigger characteristics

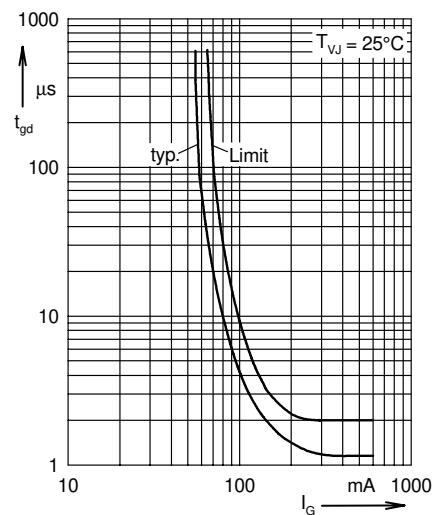


Fig. 2 Gate trigger delay time

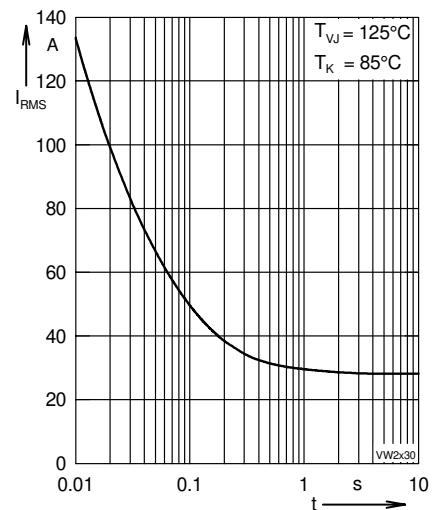


Fig. 4 Rated RMS current versus time (360° conduction)

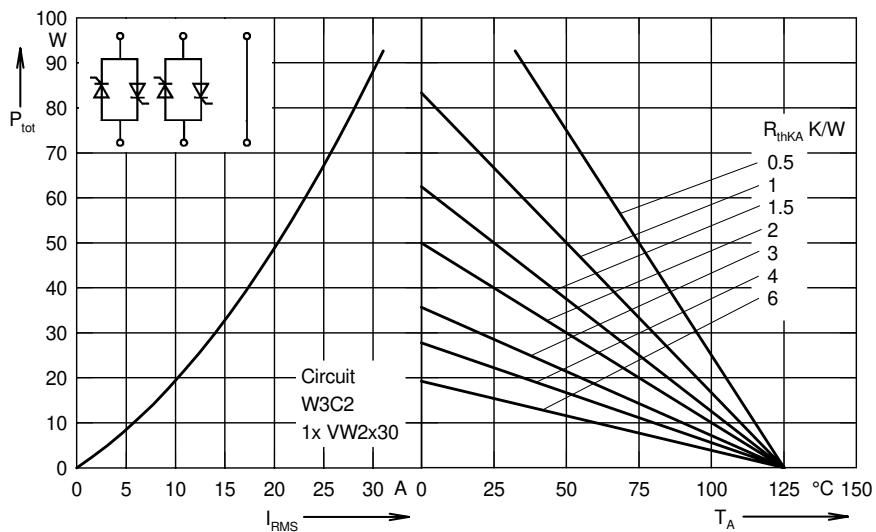


Fig. 5 Load current capability for two phase AC controller

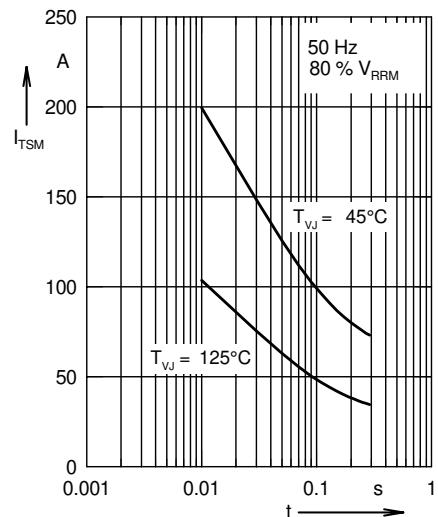


Fig. 6 Surge overload current

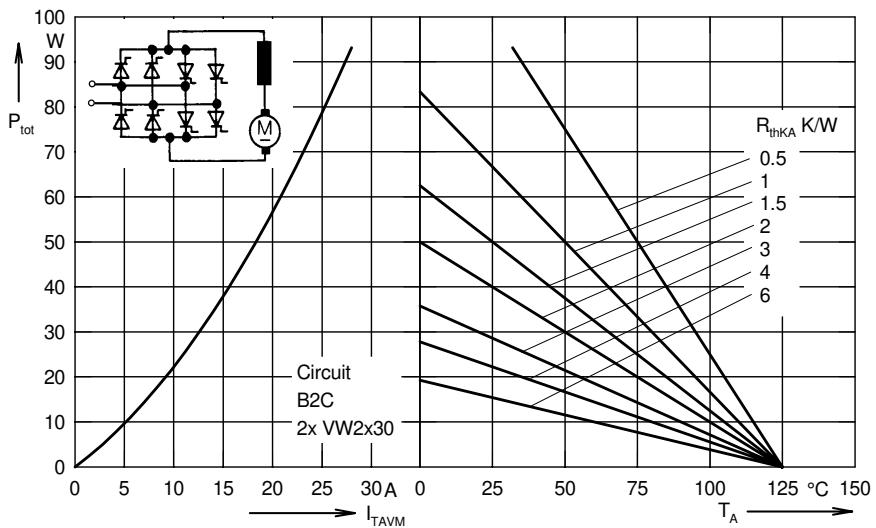


Fig. 7 Power dissipation versus direct output current and ambient temperature cyclo converter, four quadrant operation

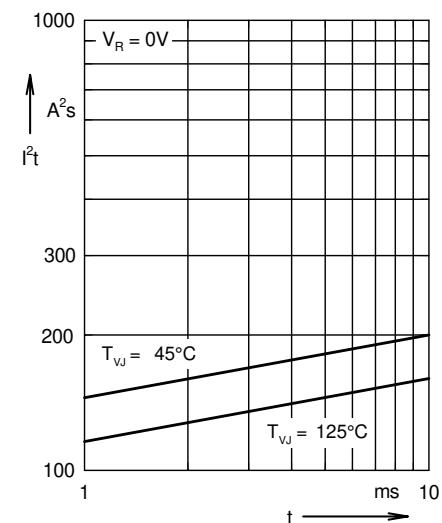


Fig. 8 I^2t versus time (per thyristor)

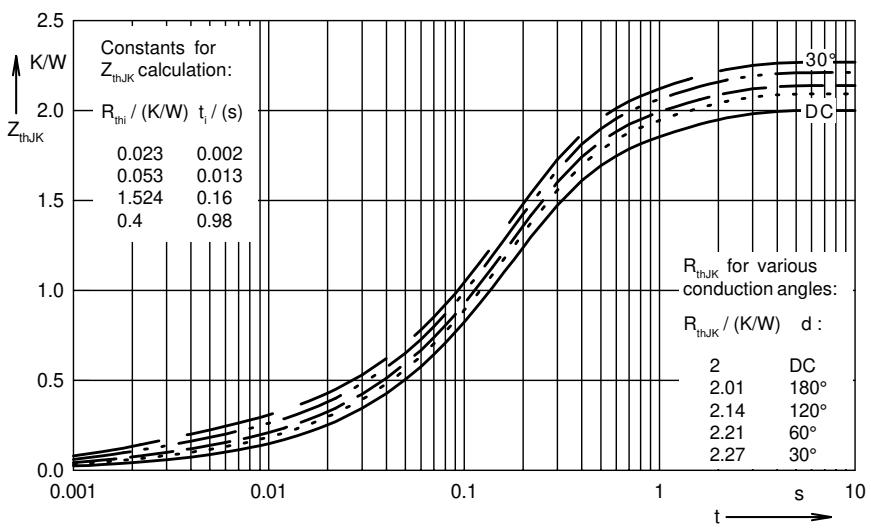


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor)

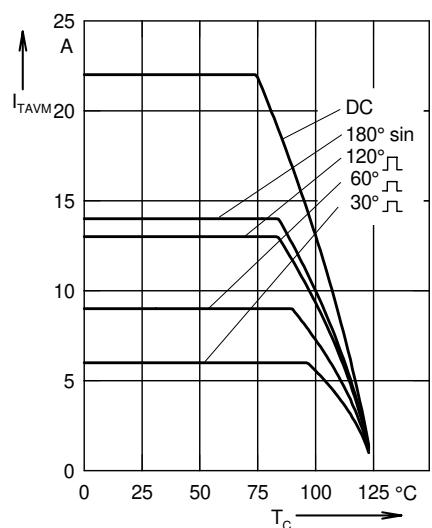


Fig. 10 Maximum forward current at case temperature